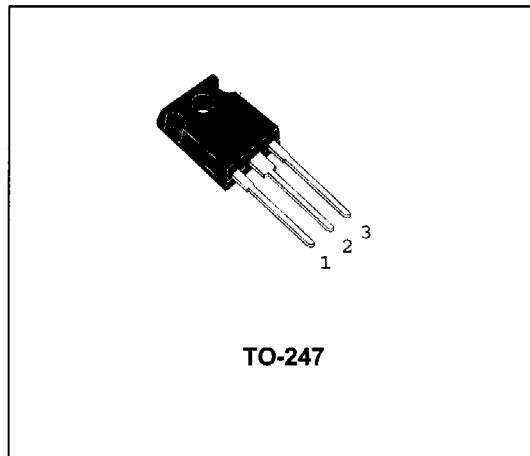


STGW20NB60H

N-CHANNEL 20A - 600V TO-247
PowerMESH™ IGBT

TYPE	V _{CES}	V _{CE(sat)}	I _C
STGW20NB60H	600 V	< 2.8 V	20 A

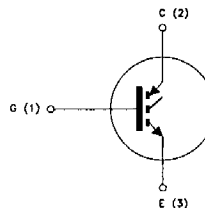
- HIGH INPUT IMPEDANCE (VOLTAGE DRIVEN)
- LOW ON-VOLTAGE DROP (V_{CESAT})
- LOW GATE CHARGE
- HIGH CURRENT CAPABILITY
- VERY HIGH FREQUENCY OPERATION
- OFF LOSSES INCLUDE TAIL CURRENT



APPLICATIONS

- HIGH FREQUENCY MOTOR CONTROLS
- WELDING EQUIPMENTS
- SMPS AND PFC IN BOTH HARD SWITCH AND RESONANT TOPOLOGIES

INTERNAL SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CES}	Collector-Emitter Voltage (V _{GS} = 0)	600	V
V _{ECR}	Emitter-Collector Voltage	20	V
V _{GE}	Gate-Emitter Voltage	± 20	V
I _C	Collector Current (continuous) at T _c = 25 °C	40	A
I _C	Collector Current (continuous) at T _c = 100 °C	20	A
I _{CM} (*)	Collector Current (pulsed)	160	A
P _{tot}	Total Dissipation at T _c = 25 °C	150	W
	Derating Factor	1.2	W/°C
T _{stg}	Storage Temperature	-65 to 150	°C
T _j	Max. Operating Junction Temperature	150	°C

(*) Pulse width limited by safe operating area

NJ Semi-Conductors reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by NJ Semi-Conductors is believed to be both accurate and reliable at the time of going to press. However, NJ Semi-Conductors assumes no responsibility for any errors or omissions discovered in its use. NJ Semi-Conductors encourages customers to verify that datasheets are current before placing orders.



STGW20NB60H

THERMAL DATA

R _{thj-case}	Thermal Resistance Junction-case	Max	0.83	°C/W
R _{thj-amb}	Thermal Resistance Junction-ambient	Max	30	°C/W
R _{thc-h}	Thermal Resistance Case-heatsink	Typ	0.1	°C/W

ELECTRICAL CHARACTERISTICS (T_j = 25 °C unless otherwise specified)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{BR(CE)}	Collector-Emitter Breakdown Voltage	I _C = 250 µA V _{GE} = 0	600			V
I _{CES}	Collector cut-off (V _{GE} = 0)	V _{CE} = Max Rating T _j = 25 °C V _{CE} = Max Rating T _j = 125 °C			10 100	µA µA
I _{GES}	Gate-Emitter Leakage Current (V _{CE} = 0)	V _{GE} = ± 20 V V _{CE} = 0			± 100	nA

ON (*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{GE(th)}	Gate Threshold Voltage	V _{CE} = V _{GE} I _C = 250 µA	3		5	V
V _{CE(SAT)}	Collector-Emitter Saturation Voltage	V _{GE} = 15 V I _C = 20 A V _{GE} = 15 V I _C = 20 A T _j = 125 °C		2.3 1.9	2.8	V V

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g _{fs}	Forward Transconductance	V _{CE} = 25 V I _C = 20 A	7.0	10		S
C _{ies} C _{oes} C _{res}	Input Capacitance Output Capacitance Reverse Transfer Capacitance	V _{CE} = 25 V f = 1 MHz V _{GE} = 0	1200 140 28	1700 200 40	2200 260 52	pF pF pF
Q _G Q _{GE} Q _{GC}	Total Gate Charge Gate-Emitter Charge Gate-Collector Charge	V _{CE} = 480 V I _C = 20 A V _{GE} = 15 V		110 13 51	145	nC nC nC
I _{CL}	Latching Current	V _{clamp} = 480 V R _G = 10 Ω T _j = 150 °C	80			A

SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
t _{d(on)} t _r	Delay Time Rise Time	V _{CC} = 480 V I _C = 20 A V _{GE} = 15 V R _G = 10 Ω		20 70		ns ns
(di/dt) _{on}	Turn-on Current Slope	V _{CC} = 480 V I _C = 20 A R _G = 10 Ω V _{GE} = 15 V		350		A/µs
E _{on}	Turn-on Switching Losses	T _j = 125 °C		300		µJ

TO-247 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.7		5.3	0.185		0.209
D	2.2		2.6	0.087		0.102
E	0.4		0.8	0.016		0.031
F	1		1.4	0.039		0.055
F3	2		2.4	0.079		0.094
F4	3		3.4	0.118		0.134
G		10.9			0.429	
H	15.3		15.9	0.602		0.626
L	19.7		20.3	0.776		0.779
L3	14.2		14.8	0.559		0.582
L4		34.6			1.362	
L5		5.5			0.217	
M	2		3	0.079		0.118

